

MA6X126

Silicon epitaxial planar type

For switching circuits

■ Features

- Four-element contained in one package, allowing high-density mounting
- High breakdown voltage ($V_R = 80$ V)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---|-------------|-------------|------------------|
| Reverse voltage (DC) | V_R | 80 | V |
| Peak reverse voltage | V_{RM} | 80 | V |
| Average forward current* ¹ | $I_{F(AV)}$ | 100 | mA |
| Peak forward current* ¹ | I_{FM} | 225 | mA |
| Non-repetitive peak forward surge current* ^{1,2} | I_{FSM} | 500 | mA |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Note) *1 : Value for single diode

*2 : $t = 1$ s

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

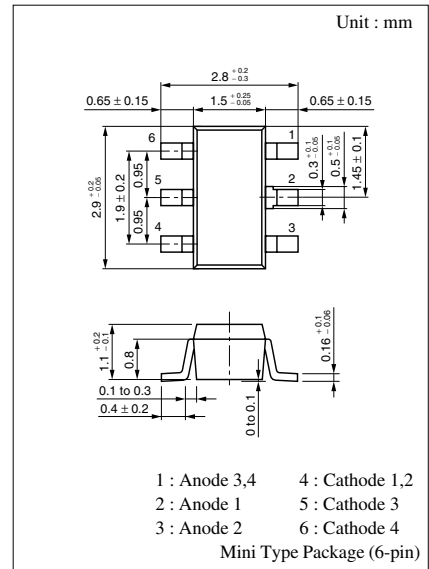
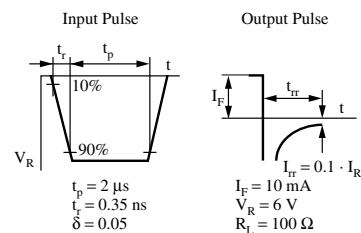
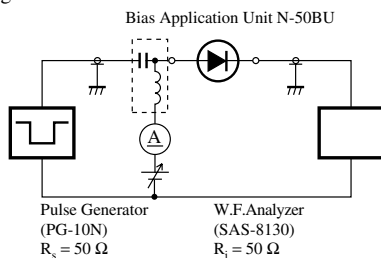
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|-------------------------------------|--------------------------|---|-----|-----|-----|------|
| Reverse current (DC) | I_R | $V_R = 75$ V | | | 100 | nA |
| Forward voltage (DC) | V_F | $I_F = 100$ mA | | | 1.2 | V |
| Reverse voltage (DC) | V_R | $I_R = 100$ μA | 80 | | | V |
| Terminal capacitance | C_{i1} * ¹ | $V_R = 0$ V, $f = 1$ MHz | | | 15 | pF |
| | C_{i2} * ² | $V_R = 0$ V, $f = 1$ MHz | | | 2 | pF |
| Reverse recovery time* ³ | t_{rr1} * ¹ | $I_F = 10$ mA, $V_R = 6$ V | | | 10 | ns |
| | t_{rr2} * ² | $I_{rr} = 0.1 \cdot I_R$, $R_L = 100$ Ω | | | 3 | |

Note) 1. Rated input/output frequency: 100 MHz

2. *1 : Between pins 1 and 5, Between pins 1 and 6

*2 : Between pins 4 and 2, Between pins 4 and 3

*3 : t_{rr} measuring circuit



Marking Symbol: M2S

Internal Connection

